



# N-Channel 100-V (D-S) 175°C MOSFET

## PRODUCT SUMMARY

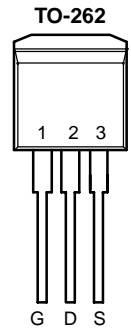
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
100	0.0105 @ $V_{GS} = 10$ V	85 <sup>a</sup>
	0.012 @ $V_{GS} = 4.5$ V	

## FEATURES

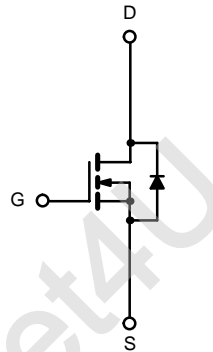
- TrenchFET® Power MOSFET
- 175°C Junction Temperature

## APPLICATIONS

- DC/DC Primary Side Switch



Top View  
SUV85N10-10



N-Channel MOSFET

## ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	$V_{DS}$	100	V	
Gate-Source Voltage	$V_{GS}$	±20		
Continuous Drain Current (T <sub>J</sub> = 175°C)	$I_D$	T <sub>C</sub> = 25°C	85 <sup>a</sup>	A
		T <sub>C</sub> = 125°C	60 <sup>a</sup>	
Pulsed Drain Current	$I_{DM}$	240		
Avalanche Current	$I_{AR}$	75		
Repetitive Avalanche Energy <sup>b</sup>	L = 0.1 mH	$E_{AR}$	280	mJ
Maximum Power Dissipation <sup>b</sup>	$P_D$	T <sub>C</sub> = 25°C	250 <sup>c</sup>	W
		T <sub>A</sub> = 25°C <sup>d</sup>	3.75	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C	

## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit	
Junction-to-Ambient	$R_{thJA}$	PCB Mount <sup>d</sup>	40	°C/W
		Free Air	62.5	
Junction-to-Case	$R_{thJC}$	0.6		

### Notes

- Package limited.
- Duty cycle ≤ 1%.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS (T <sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	100			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1		3	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	
		V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	120			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A		0.0085	0.0105	Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A		0.0010	0.012	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A, T <sub>J</sub> = 125 °C			0.017	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A, T <sub>J</sub> = 175 °C			0.022	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A	25			S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		6550		pF
Output Capacitance	C <sub>oss</sub>			665		
Reverse Transfer Capacitance	C <sub>rss</sub>			265		
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 85 A		105	160	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			17		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			23		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 50 V, R <sub>L</sub> = 0.6 Ω I <sub>D</sub> ≅ 85 A, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 2.5 Ω		12	25	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			90	135	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			55	85	
Fall Time <sup>c</sup>	t <sub>f</sub>			130	195	
<b>Source-Drain Diode Ratings and Characteristics (T<sub>C</sub> = 25 °C)<sup>b</sup></b>						
Continuous Current	I <sub>S</sub>				85	A
Pulsed Current	I <sub>SM</sub>				240	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 85 A, V <sub>GS</sub> = 0 V		1.0	1.5	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 50 A, di/dt = 100 A/μs		85	140	ns
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>			4.5	7	A
Reverse Recovery Charge	Q <sub>rr</sub>			0.17	0.35	μC

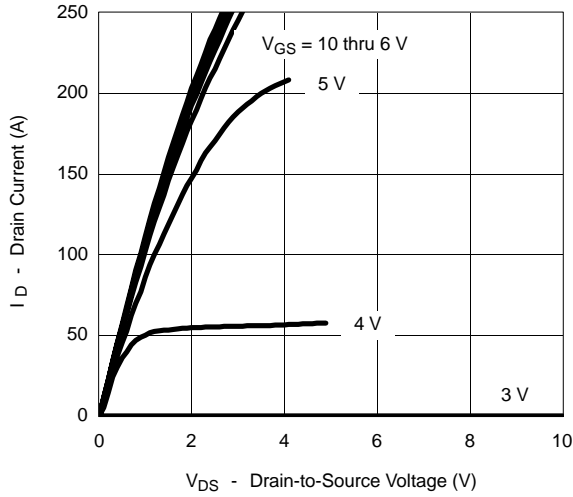
## Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

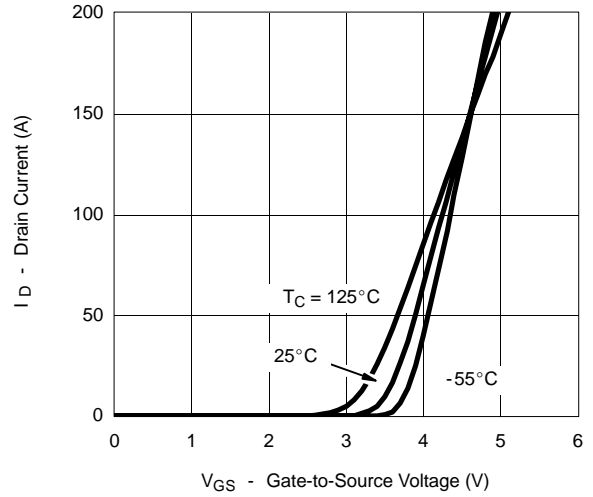


**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

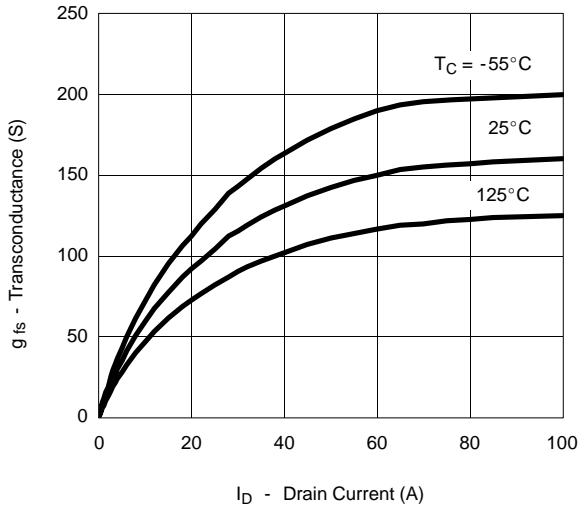
**Output Characteristics**



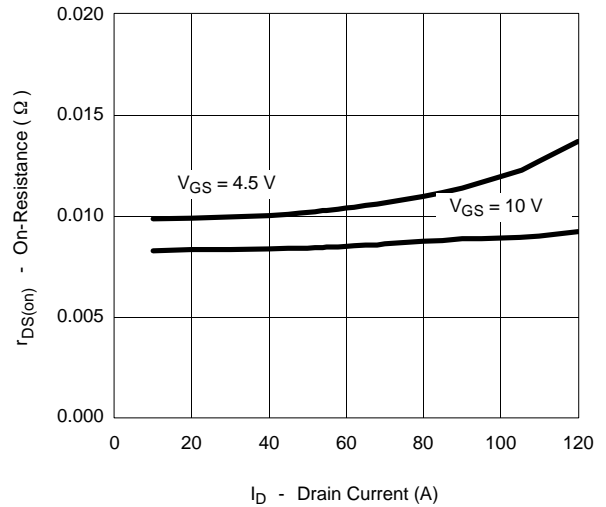
**Transfer Characteristics**



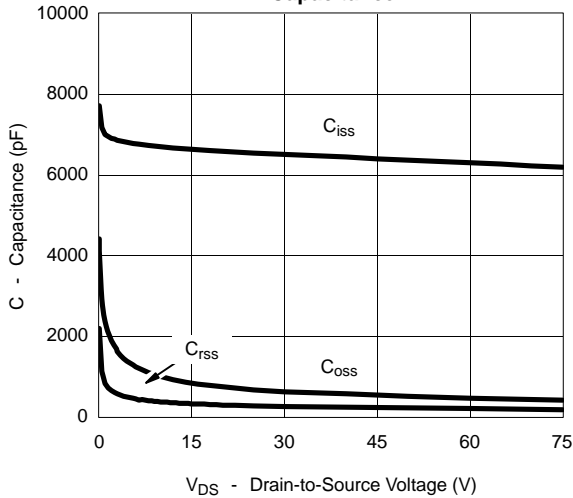
**Transconductance**



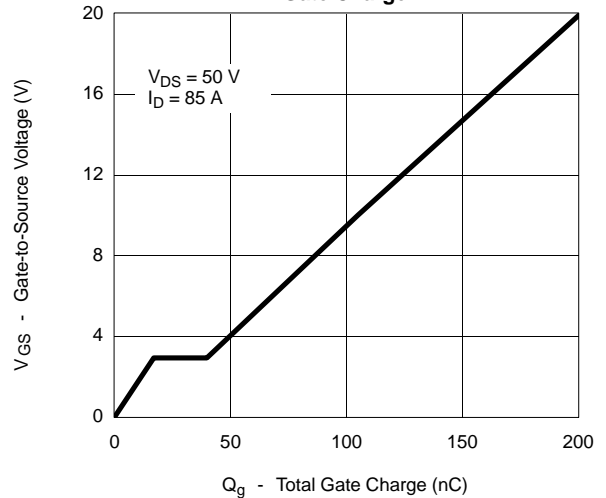
**On-Resistance vs. Drain Current**



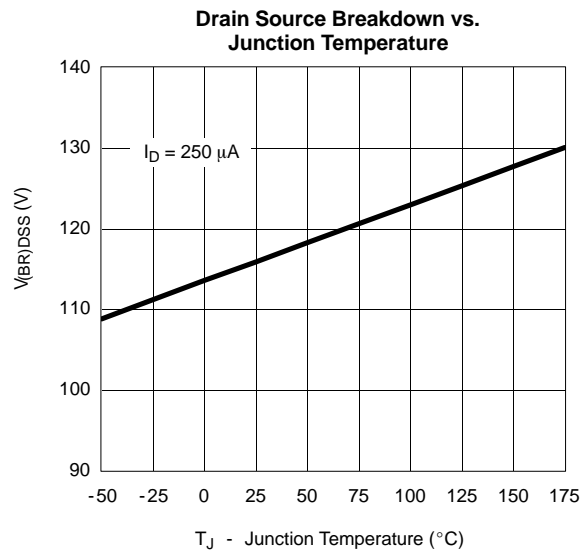
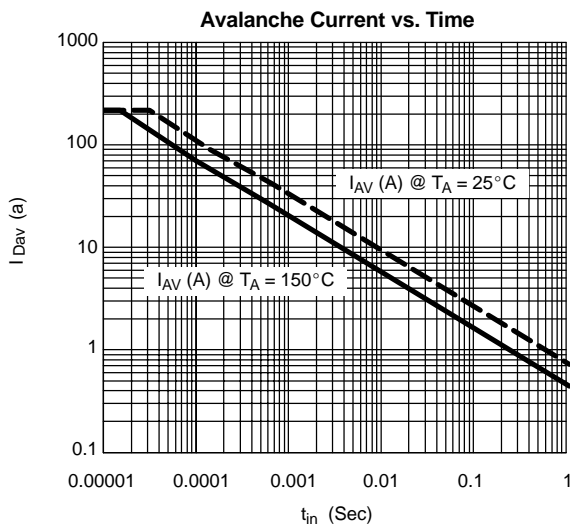
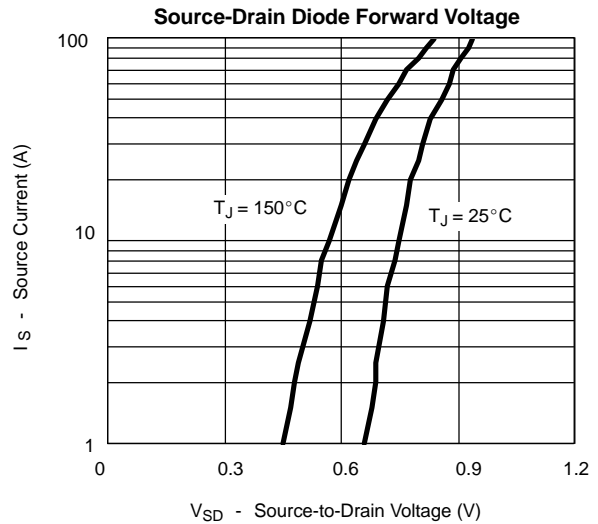
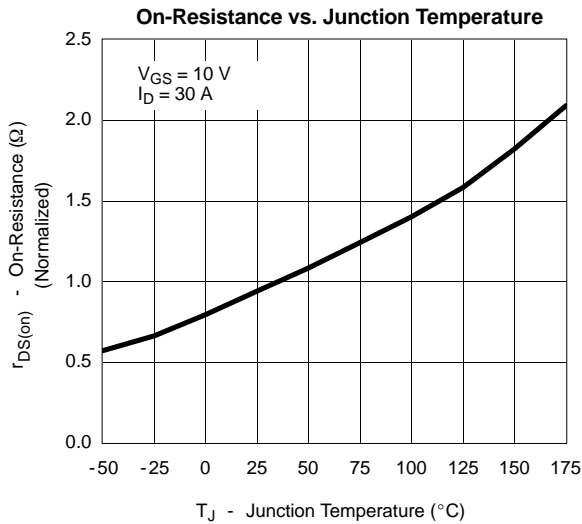
**Capacitance**



**Gate Charge**



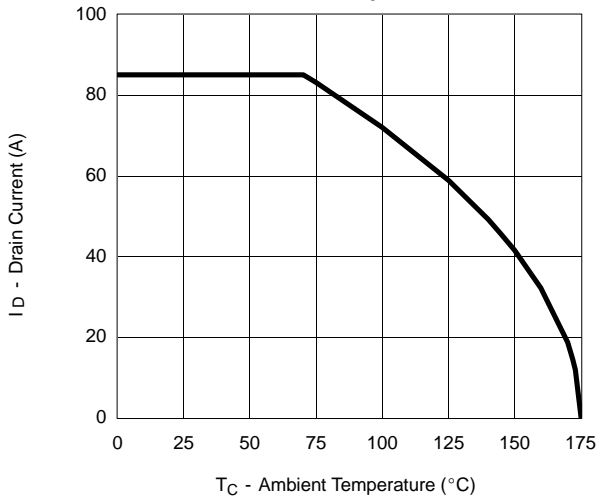
### TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



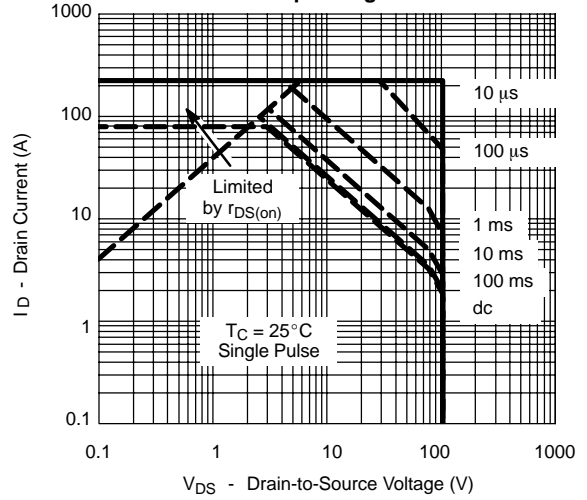


**THERMAL RATINGS**

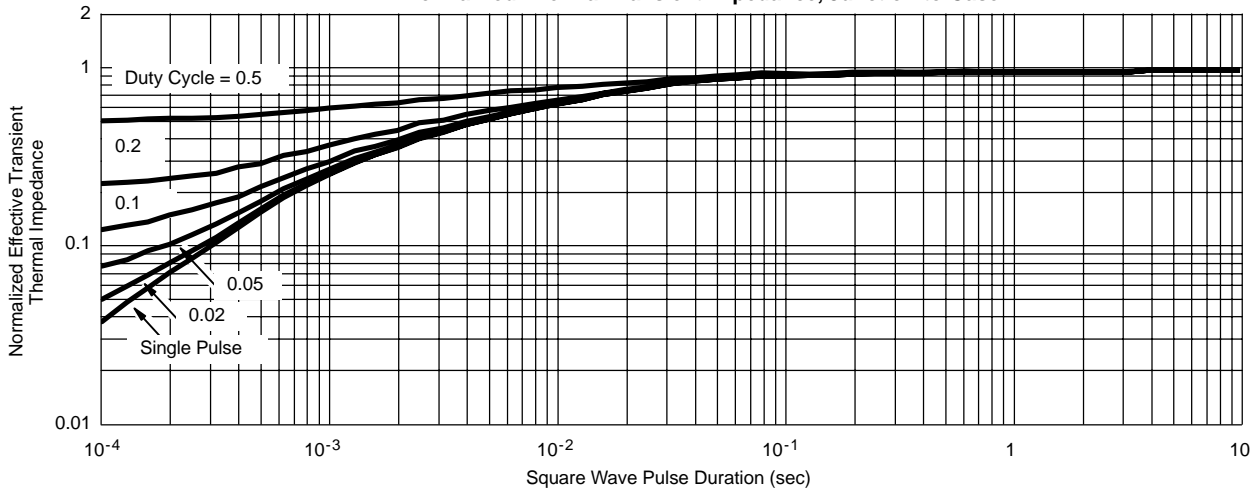
Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case





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